

Amendments to the Claims:

The listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

Claims 1.-16. (Cancelled)

Claim 17. (New) MEMS switch having a bent switching element, comprising:

a signal conductor arranged on a substrate;

an oblong-shaped switching element, which has a bent elastic bending area and is fastened in a cantilevered manner on the substrate; and

an electrode arrangement for generating an electrostatic force that acts upon the switching element and bends it toward the signal conductor; wherein,

the switching element includes at least two switching arms having a bent elastic bending area;

the switching arms are arranged on both sides of the signal conductor parallel thereto;

free ends of the switching arms are mutually connected by a bridge that is positioned over the signal conductor;

the switching arms are configured such that under the effect of the electrostatic force, the respective elastic bending areas progressively approach the electrode arrangement in a direction parallel to the signal conductor.

Claim 18. (New) The high-frequency MEMS switch according to Claim 17, wherein the bridge forms a contact area.

Claim 19. (New) The high-frequency MEMS switch according to Claim 17, wherein the electrode arrangement comprises at least one ground electrode arranged under the switching element flatly on the substrate to electrostatically attract the switching element.

Claim 20. (New) The high-frequency MEMS switch according to Claim 17, wherein the electrode arrangement comprises one of a ground electrode arranged below the substrate, and the substrate itself.

Claim 21. (New) The high-frequency MEMS switch according to Claim 17, wherein the electrode arrangement extends parallel to the substrate surface in order to pull the switching element by the electrostatic force in its bending area progressively toward the substrate surface.

Claim 22. (New) The high-frequency MEMS switch according to Claim 17, wherein the bent bending area is formed of bimorphic material.

Claim 23. (New) The high-frequency MEMS switch according to Claim 17, wherein the bending area has a surface melted-on by laser heating for generating a tensile stress.

Claim 24. (New) The high-frequency MEMS switch according to Claim 17, wherein the switching element is produced by thin-film technology.

Claim 25. (New) The high -frequency MEMS switch according to Claim 17, wherein under the effect of the electrostatic force, the contact area comes in direct contact with the signal conductor.

Claim 26. (New) The high-frequency MEMS switch according to Claim 17, wherein under the effect of the electrostatic force, the contact area takes up a minimal distance from the signal conductor.

Claim 27. (New) A method of producing a high-frequency MEMS switch having a bent switching element, said method comprising:

constructing a signal conductor on a substrate;

constructing an electrode arrangement on the substrate;

forming an oblong switching element having a bent elastic bending area on the substrate such that, in the bending area, it is pulled by the electrode arrangement by an electrostatic force lengthwise toward the substrate and, by an elastic restoring force, in the bending area, moves away from the substrate; wherein,

the switching element has at least two switching arms, each having a bent elastic bending area, which are arranged on both sides of the signal conductor parallel thereto, and are mutually connected at a free end by a bridge positioned over the signal conductor;

the switching arms are configured such that, under the effect of the electrostatic force, the respective elastic bending areas progressively approach the electrode arrangement in a direction parallel to the signal conductor.

Claim 28. (New) The method according to Claim 27, wherein the bridge forms a contact area.

Claim 29. (New) The method according to Claim 27, wherein at least one ground electrode arranged below the substrate forms the electrode arrangement .

Claim 30. (New) The method according to Claim 27, wherein the surface of the bending area is melted on by laser heating for generating a tensile stress.

Claim 31. (New) The method according to Claim 27, wherein the electrode arrangement is formed by at least one intrinsically conducting substrate area or by one intrinsically conducting substrate.